

## PATENT ABSTRACTS OF JAPAN

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(21)Application number : 50-125752 (71)Applicant : HITACHI LTD  
(22)Date of filing : 18.10.1975 (72)Inventor : HONMA YOSHIO  
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(54) PROCESS FOR PRODUCTION OF SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To form a serration-free surface and make a semiconductor device of high scale of integration, by coating the undulated surface of an Si substrate with a predetermined coating layer and subjecting same to sputteretching.

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### LEGAL STATUS

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